

## COMPLETE LISTING OF ALL CLAIMS

1      Claim 1. (currently amended) A process for creating an electrically isolated electrode on a  
2      sidewall of a cavity in a base, the process comprising the steps of:  
3      etching one or more trenches in a backside of the base wherein the base is part of a  
4      starting material;  
5      forming a layer of insulating material on one or more sidewalls of one or more of the  
6      trenches;  
7      forming a conductive layer on the layer of insulating material on one or more  
8      sidewalls of one or more of the trenches;  
9      depositing material on or removing material from a front side of the starting material  
10     that is different from the backside of the base; and;  
11     removing base material from a portion of the base bordered by the one or more  
12     trenches.

1      Claim 2. (original) The process of claim 1, wherein the trenches are defined underneath a  
2      flap.

1      Claim 3. (original) The process of claim 1, wherein the trench etch stops on an etch-stop  
2      layer.

1      Claim 4. (original) The process of claim 1, wherein the conductive layer completely fills the  
2      trench.

1      Claim 5. (original) The process of claim 1, wherein a layer of conducting material is also  
2      deposited on the backside of the base.

1      Claim 6. (original) The process of claim 1, wherein the trench is formed using an  
2      anisotropic etch.

1      Claim 7. (original) The process of claim 1, wherein the base is a crystalline material.

1      Claim 8. (original) The process of claim 1 wherein the trench is etched such that an  
2      orientation of the sidewall is defined by a crystal orientation of the base material.

1      Claim 9. (original) The process of claim 8, wherein the base is composed of crystalline  
2      silicon having a <110> crystal orientation.